

Appl. No.: 10/561,883

Amdt. Dated: December 2, 2009

Reply to Office Action of September 2, 2009

In the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1—24 (Cancelled)

25. (Currently Amended) A method of die bonding comprising the steps of:

- a. providing a structure comprising a wafer substrate separated from carrier base means by ~~[[an]]~~ a second adhesive ~~[[layer]]~~ adhered to the carrier base means by a first adhesive between the carrier base and the second adhesive ~~[[layer]]~~;
- b. laser machining through the wafer substrate, the first adhesive and through the second adhesive ~~layer no more than~~ and at most to scribe the carrier base means to form a singulated die with an attached singulated adhesive layer;
- c. curing the structure to release the attached singulated adhesive layer from the carrier base means by curing the first adhesive;
- d. picking and placing the die and attached singulated adhesive layer on a die pad; and
- e. curing the attached singulated adhesive layer to adhere the die to the die pad.

26. (Currently Amended) A method as claimed in claim 25, wherein the step of laser machining comprises laser machining the wafer substrate using a first laser beam with a first machining profile of selected laser pulse power, laser pulse repetition rate, laser pulse width, laser beam scanning speed and laser wavelength; using a second laser beam with a second such machining profile to machine the adhesive layer and using a third laser beam with a third such machining profile to machine the carrier base means such that a speed of machining is maximised while providing a predetermined quality of singulated dies without substantial delamination of the second adhesive ~~[[layer]]~~ and the carrier base means or substantial production of burrs.

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27. (Previously Presented) A method as claimed in claim 26, wherein at least two of the first machining profile, the second machining profile and the third machining profile are a same machining profile.
28. (Currently Amended) A method as claimed in claim 25, wherein the step of curing the structure comprises curing the first adhesive with ultraviolet light.
29. (Currently Amended) A method as claimed in claim 25, wherein the step of curing the attached singulated adhesive layer comprises heat curing the second adhesive [[layer]].
30. (Currently Amended) A method as claimed in claim 25, wherein the step of machining the wafer substrate comprises machining a blind via in the wafer substrate or a via through the wafer substrate and the second adhesive [[layer]].
31. (Previously Presented) A method as claimed in claim 25, wherein the step of laser machining includes a further step, after laser machining, of washing the structure to remove accumulated laser machining debris from the singulated die.
32. (Previously Presented) A method as claimed in claim 31, wherein the step of providing a structure comprises providing a structure having a protective film to protect the structure from debris produced during laser machining and the step of washing the structure comprises removing the protective film and accumulated debris thereon.
33. (Previously Presented) A method as claimed in claim 25, wherein the step of providing a structure comprises providing a structure having a wafer substrate less than 800 microns thick.
34. (Previously Presented) A method as claimed in claim 25, wherein the step of laser machining comprises providing an assist gas environment for laser machining.

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35. (Previously Presented) A method as claimed in claim 34, wherein the step of providing an assist gas environment comprises providing a gas environment in which photo- dissociation produces active radicals.
36. (Previously Presented) A method as claimed in claim 34, wherein the step of providing a gas environment reduces deposition of solid machining debris around a laser-machining site.
37. (Previously Presented) A method as claimed in claim 25, wherein the carrier base means is one of: a dicing tape, an inflexible tape suitable for thin wafer dicing or backgrinding; and a glass or other transparent solid.
38. (Currently Amended) A method as claimed in claim 25, wherein the step of providing a structure comprises providing a structure including a wafer substrate separated facedown from substantially inflexible transparent backgrinding tape means by the second adhesive [[layer]] and the step of laser machining is performed subsequent to backgrinding the wafer substrate.
39. (Previously Presented) A method as claimed in claim 25, wherein the step of picking and placing the die and attached singulated adhesive layer comprises picking and placing the die and attached singulated adhesive layer on another die to form a multistack die package.
40. (Currently Amended) A die bonding apparatus comprising: laser machining means arranged for machining a wafer substrate and [[an]] a second adhesive [[layer]] adhered to the wafer substrate and attached to carrier base means by a first adhesive between the carrier base means and the second adhesive [[layer]] and ~~for no more than~~ at most scribing underlying carrier base means to form a singulated die with a singulated adhesive layer; first curing means arranged for curing the first adhesive to release the singulated adhesive layer from the carrier base means; ~~pick and place means arranged for picking the singulated die and~~

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~~adhesive layer from the carrier base means and placing the singulated die and adhesive layer on die pad means and second curing means arranged for curing the singulated adhesive layer of the singulated die to adhere the singulated die to the die pad means.~~

41. (Previously Presented) A die bonding apparatus as claimed in claim 40, wherein the laser machining means comprises: laser source means arranged for providing a pulsed laser beam; laser beam scanning means; and control means arranged for controlling at least one of laser pulse energy, laser wavelength, laser repetition frequency, laser pulse width, laser beam scanning speed and a number of scans by the pulsed laser beam.
42. (Previously Presented) A die bonding apparatus as claimed in claim 41, wherein the laser machining means further comprises memory means for storing a machining profile of at least one of laser pulse energy, laser wavelength, laser repetition frequency, laser pulse width, laser beam scanning speed and a number of scans by the pulsed laser beam, for use by the control means.
43. (Previously Presented) A die bonding apparatus as claimed in claim 40, wherein the first curing means comprises ultraviolet curing means.
44. (Previously Presented) A die bonding apparatus as claimed in claim 40, wherein the second curing means comprises heat curing means.
45. (Previously Presented) A die bonding apparatus as claimed in claim 40, including washing means arranged for washing laser machining debris from the singulated die.
46. (Previously Presented) A die bonding apparatus as claimed in claim 45, wherein the wafer substrate is provided with a protective film to protect the wafer substrate from laser machining debris, and the washing means is arranged to remove the protective film from the singulated die.

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47. (Previously Presented) A die bonding apparatus as claimed in claim 40, adapted for carrier base means which is one of: a dicing tape, an inflexible tape suitable for thin wafer dicing or backgrinding; and a glass or other transparent solid.
48. (Previously Presented) A die bonding apparatus as claimed in claim 40, adapted for machining a structure comprising a wafer substrate separated facedown from substantially inflexible transparent backgrinding tape means by the adhesive layer.